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Communication

Structural, electronic, elastic and vibrational properties of two dimensional graphene-like BN under high pressure



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ABSTRACT

The structural, electronic, elastic and vibrational properties of boron nitride (BN) were analyzed using ab initio computational methods based on density functional theory. The exchange-correlation energy functional was evaluated using the local density approximation (LDA) under pressure. BN crystallizes in hexagonal structure (h-BN) with symmetry P6₃/mmc. The structural transform was obtained at the BN from h-BN transformed into wurtzite (w-BN) with symmetry P6₃mc at 12.5 GPa. During this phase transformation, intermediate states with space group $P\overline{3}m1$ and P3m1were observed. Besides, the electronic properties for the obtained stable phases of BN were calculated. Both structures have a semiconductor character with a direct band gap. We also made elastic and phonon calculations to understand the mechanical and dynamically stability of the obtained phases of BN. BN is stable in both phases. As a result of the literature searches, the obtained intermediate states were first predicted in this study. Thus, we believe that this study will guide the experimental studies to be conducted.

1. Introduction

In recent years, some theoretical [1-6] and experimental [7-16]studies have been carried out to investigate the physical and chemical properties of crystalline BN. BN is a III-V semiconductor compound with a structure very similar to graphite is a synthetically produced compound and has remarkable and useful properties in a wide range of applications such as deep ultraviolet emitter, transparent membrane, the dielectric layer, or protective coatings [17-19]. In previous studies on BN, it was revealed that the stable structure of BN was hexagonal in ambient conditions and the cubic and wurtzite structure was synthesized from the hexagonal structure at high temperature and pressure [7,8]. Some subsequent experimental studies have found that the cubic phase of BN is thermodynamically stable under ambient conditions and that hexagonal BN is stable at elevated temperatures (T = $900-1500^{\circ}$) [12–14]. The possible scenarios on the transition of the phase stability from the hexagonal to the cubic structure are discussed, but this issue is inconclusive.

BN has four polymorphs: (I) the hexagonal structure (h-BN), analogous to graphite, with space group $P6_3/mmc$, (II) the rhombohedral structure (r-BN) with space group R3m. These structures have a two-dimensional (2D) layered structure consisting of sp^2 bonds. (III) the

zinc blende structure (z-BN) with space group $F\overline{4}3m$, (IV) the wurtzite structure (w-BN) with space group P6₃mc. These structures have threedimensional modifications consisting of sp³ bonds and can be easily synthesized under high pressure and temperature [9,10,20–24].

In this study, we examined a graphite-like hexagonal structure which is the most stable phase of BN under high pressure. This structure of BN has a P6₃/mmc space group in ambient conditions. It was observed that when the increased pressure was applied above this structure, the h-BN structure changed into another hexagonal wurtzite structure, the dense diamond-like modifications, with space group P6₃mc [2,9,10]. Two trigonal intermediate states with space groups $P\overline{3}m1$ and P3m1 were predicted during this transition.

We calculated the electronic properties for both phases of BN. The h-BN and w-BN forms of BN have a wide band gap. They can be used in many technological fields with this feature. We have also calculated elastic and vibrational properties to determine the mechanical and dynamically stability of obtained phases of BN.

Besides, the graphene layers have three different stacking modes. AA-stacking with a simple hexagonal structure, AB-stacking with orthorhombic structure and ABC-stacking with rhombohedral structure. There is a small energy barrier between the AB- and AA-stacking. Therefore, in general, natural graphite adopts the AB-stacking

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Fig. 1. The graph of the change of simulation cell volume as the function of the pressure.



Fig. 2. Crystal structures of BN: $P6_3$ /mmc phase of BN (left) at zero pressure and $P6_3$ mc phase of BN (right) at 90 GPa.



Fig. 3. Energy-volume graph for the stable phases of the BN compound.



Fig. 4. Enthalpy graph for the stable phases of BN as the function of the pressure.

sequence [25] and there are also many theoretical and experimental studies on the AB-stacking sequence [26–33]. On the other hand, due to the lack of practical samples and associated with experimental observations, there is little theoretical work on the AA-stacking [34,35]. Very recently, however, Liu et al. [36] surprisingly found that bilayer graphene shows AA-stacking, which is often difficult to distinguish from monolayer graphene. As a result, it is necessary to do more research, both theoretically and experimentally, on the physical properties of AA-stacking BN [37].

Therefore, in this paper, we will perform ab-initio calculations on structural, electronic, mechanic and vibrational properties of AA stacking BN. We believe that our results will guide people who want to work experimentally.

2. Methods

The structural, electronic, elastic and vibrational properties of BN were carried out within Density Functional Theory (DFT) calculations using Siesta software package [38]. The calculations were performed using an LDA-CA exchange-correlation functional [39]. We have used Troullier-Martins type norm-conserving pseudo-potential for B and N atoms [40]. In all calculations were conducted using double-zeta plus polarized (DZP) basis sets of localized atomic orbitals. The energy mesh cut-off, which corresponds to the spacing of the real space grid used to calculate the Hartree, exchange, and correlation contribution to the total energy and Hamiltonian, was set to be 350 Rydberg (Ry). BN was modelled using 3x3x2 cells with periodic boundary condition for 72 atoms supercells. The Brillouin zones (BZ) were sampled with the 10x10x4 Monkhorst-Pack k-point mesh [41]. Structural optimizations were performed via the conjugate-gradient (CG) method until the residual force acting on all atoms were smaller than 0.01 eV/Å and pressure is gradually increased by 10 GPa through this method to the system. For analyze each minimization step, we used the KPLOT program and the RGS algorithm that give detailed information about the space groups, atomic positions and lattice parameters of an analyzed structure [42,43].

3. Results and discussions

BN with lattice parameters a = b = 2.4880 Å and c = 6.2543 Å under

Table 1

The values of transition pressure, lattice parameter, c/a ratio, volume, bulk modulus and derivate of bulk modulus for P63/mmc and P63mc phases of BN.

Phases	P _T (GPa)	a = b (Å)	c (Å)	c/a	V (Å ³ /atom)	B ₀ (GPa)	$\mathbf{B}_{0}^{'}$	References
P63/	0	2.4880	6.2543	2.5138	8.380	202.87	3.8272	This study
mmc		2.4890	6.5010	2.6118	8.630	145.00		[52]
		2.5130	6.4330	2.5600	8.802	185.30		[53]
		2.4940	6.6600	2.6704		335.00	2.4800	[54]
P6 ₃ mc	12.5	2.5244	4.1619	1.6487	5.740	410.16	3.4301	This study
		2.4700	3.9800	1.6070		406.00	3.8600	[55]
	14.0	2.5500	4.2000					[56]
		2.5360	4.1900			390.00	6.3000	[54]
		2.5580	4.2280	1.6530		376.31	3.5820	[57]
	8.5							[58]
	10.4							[59]



Fig. 5. Formation of P6₃mc phase of BN at 90 GPa.

a pressure of 0 GPa crystallizes in hexagonal type structure with space group P6₃/mmc and has 4 atoms in the unit cell. The B atoms are occupied the Wyckoff 2d (1/3, 2/3, 3/4) positions while the N atoms are occupied the Wyckoff 2c (1/3, 2/3, 1/4) positions. In this study, the BN compound was first equilibrated after optimizing and then gradually increased pressures of 10 GPa up to a pressure value of 150 GPa (0, 10, 20, 30 ... 150 GPa) were applied to the equilibrium structure. We observed that when increasing pressure was applied on the structure of BN having the P6₃/mmc space group, it turned into another hexagonal wurtzite type structure having a = b = 2.5244 Å and c = 4.1619 Å lattice parameters at 90 GPa. This structure has P6₃mc space group. These structures obtained under high pressure are given in Fig. 1.

In order to examine the thermodynamic nature of the phase transformation obtained in the presence of a pressure of 90 GPa, reduced volume values corresponding to each pressure applied to the system were obtained. Using the obtained data, the pressure-reduced volume graph was plotted and given in Fig. 2. As can be seen from Fig. 2, there is a significant decrease in volume during the phase transition. This sharp decrease indicates that the phase transformation is first degree.

To determine which of the structures obtained for the BN compound is most stable, we discussed the changes in energy and volume at this stage of the study, and as a result of the calculations, we plotted the energy-volume curve given in Fig. 3. The data obtained in the calculations were fit to the third-order Birch-Murnaghan equation of state [44, 45] given in below.

$$P = 1.5B_0 \left[\left(\frac{V}{V_0} \right)^{-\frac{7}{3}} - \left(\frac{V}{V_0} \right)^{-\frac{5}{3}} \right] x \left\{ 1 + 0.75 \left(\dot{B_0} - 4 \right) \left[\left(\frac{V}{V_0} \right)^{-\frac{2}{3}} - 1 \right] \right\}$$
(1)

where P is the pressure, V is the deformed volume, V_0 is the reference volume, B_0 is the bulk modulus, and B_0 is pressure derivative of the bulk modulus.

The transition pressure value obtained under the hydrostatic pressure is generally higher than the transition pressure value obtained from the experimental studies. As a result of the simulation, the system is faced with a significant energy barrier at the transition from one phase to another phase and tries to pass this barrier to achieve the phase transition. Thus, the system is exposed to excessively pressure [46–49].

The Gibbs free energy was used to determine the most thermodynamically stable phase at the given pressure and temperature. The Gibbs free energy is given as follows.

$$G = E_{tot} + PV - TS \tag{2}$$

E is the total energy, P is the pressure, V is the volume and S is the entropy. This study was carried out in the presence of 0 K temperature. Thus, in the Gibbs free energy given in Equation (2), the term TS disappears and it is equal to the enthalpy given by equation (3).

$$H = E_{tot} + PV \tag{3}$$

where $P = dE_{tot}/dV$.

Instead of the high-pressure value obtained by simulation, we can now obtain the transition pressure values which are in good agreement with the experimental results. The intersection of the enthalpy curve obtained for both $P6_3$ /mmc and $P6_3$ mc phases gives us the phase transition pressure value. To determine this value which is consistent with the experimental results, we plotted the pressure versus enthalpy graph in Fig. 4 and observed the transition pressure value as 12.5 GPa. In Table 1, the values of transition pressure, lattice parameters, c/a ratio, volume, bulk modulus and derivate of bulk modulus for h-BN and w-BN are given and compared with other studies in the literature.

Each minimization step of the w-BN structure was analyzed in detail using the KPLOT program to determine whether there was an intermediate state during this phase change obtained at 90 GPa. As a result of the analysis, we suggest that the w-BN structure proceeds through intermediate states with space groups $P\overline{3}m1$ (the calculated lattice parameters are a = 2.4050 Å, b = 2.4050 Å, c = 4.2116 Å, $\alpha = \beta = 90$ and $\gamma = 120^{\circ}$, in which two atoms B and N occupy the Wyckoff 2d (1/3, 2/3, z), z = 0.727156 and 2d (1/3, 2/3, z), z = 0.246728 sites, respectively.) at 32nd step and with space groups P3m1 (the calculated lattice parameters are a = 2.4028 Å, b = 2.4028 Å, c = 4.1494 Å, $\alpha = \beta = 90$ and $\gamma = 120^{\circ}$, in which B atoms occupy the Wyckoff 1a (0, 0, z), z = 0 and 1c (2/3, 1/3, z), z = 0.558689 sites and N atoms occupy the Wyckoff 1a (0, 0, z), z = 0.569511 and 1c (2/3, 1/3, z), z = 0.069978 sites) at 38th step. Thus, the transition path for BN was obtained as P6₃/mmc $\rightarrow P\overline{3}m1 \rightarrow$



Fig. 6. Band structure and density of states curves for BN a) $P6_3$ /mmc and b) $P6_3$ mc phase.



Fig. 7. The phonon dispersion curves for BN a) P6₃/mmc and b) P6₃mc phase.

Table 2 Elastic constants (C_{ij} in GPa) for P6₃/mmc and P6₃mc phases of BN.

Phases	C ₁₁	C ₁₂	C ₁₃	C ₃₃	C44	References
$P6_3/$	742.53	164.29	2.4281	2.5197	6.1322	This study
mmc	901.00	202.00	2.2000	26.600	5.2000	[60]
	927.00	223.00	1.0000	32.0000	7.0000	[52]
P63mc	1001.2	152.8	70.727	1100.4	424.22	This study
	944.0	149.0	83.000	1011.0	350.00	[61]
	954.9	143.0	79.100	1018.9	357.30	[62]
	990.0	148.0	63.000	1090.0	345.00	[63]

P3m1 \rightarrow P6₃mc and depicted in Fig. 5 for the evolution of the w-BN structure.

We calculated the electronic band structures along with the highsymmetry directions and corresponding total and partial DOS as a function of energy for $P6_3/mmc$ and $P6_3mc$ phases of BN. These were illustrated near the Fermi energy (E_F) level in Fig. 6 a and b for $P6_3/mmc$ phase and $P6_3mc$ phases, respectively. Fermi levels were set to be 0 eV. The symmetry points were $\Gamma - M - K - \Gamma - A - L - H$ for both h-BN and w-BN structure. According to Fig. 6, BN is a typical semiconductor, which exhibit an indirect band gap with an energy of 5.65 eV at $M \rightarrow K$ points for P6₃/mmc phase and 6.29 eV at $\Gamma \rightarrow M$ points for P6₃mc phase [50].

Furthermore, as can be seen in Figs. 6 and 7, for both $P6_3/mmc$ and $P6_3mc$ phase, the largest contribution in the range of 0 - (-10) below the Fermi energy level came from the N-2p state. In the case of lower energy values, it came from N-2s. Above Fermi energy level, the largest contribution came from B-2p.

Elastic constants (C_{ij}) are the important properties of solids, which determine the mechanical stability of crystals. So, we also calculated the elastic constants to investigate the mechanical stability of the obtained phases of BN. The obtained C_{ij} values are given in Table 2 and compared with other studies. The well-known conditions for the mechanical stability of hexagonal structures are: C44 > 0, C₁₁>|C₁₂|, (C₁₁+2C₁₂) C₃₃ > 2C₁₃² [51]. Our results given in Table II, satisfy these stability conditions for the h-BN and w-BN structures. So, these structures are

mechanically stable.

The calculated phonon-dispersion curves are shown in Fig. 7 a and b for P6₃/mmc and P6₃mc phases of BN, respectively. Since unit cells of P6₃/mmc and P6₃mc phases contain four atoms, the corresponding number of vibration modes is twelve, as seen in Fig. 7, of which three are acoustic branches and the remaining nine are optical modes. We do not find any imaginary phonon frequency in the whole Brillouin zone for P6₃/mmc and P6₃mc phases. This supports that P6₃/mmc and P6₃mc phases of BN are the dynamical stability.

4. Conclusions

In this study, ab-initio calculations were performed to examine phase transition behaviour of BN under high pressure with SIESTA. As a result of the calculations, a first-order phase transition was observed from the $P6_3$ /mmc phase to the $P6_3$ mc phase. Besides, two different intermediate states were predicted during this phase transition. These intermediate states were firstly predicted in this study. On the other hand, to much understand the physical properties of BN, electronic band structure and density of states were examined. Both $P6_3$ /mmc and $P6_3$ mc phases of BN have a semiconductor character. We also calculated elastic constants and vibrational properties of BN and found both phases mechanically and dynamically stable.

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